



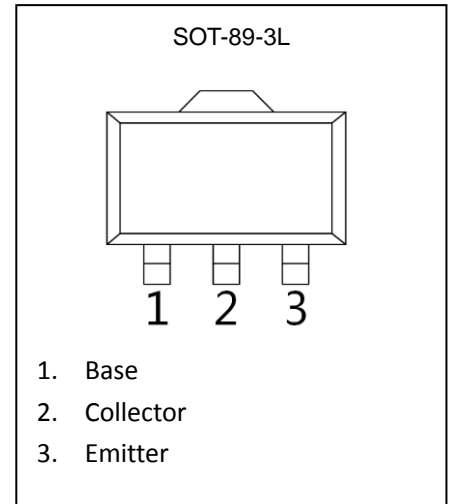
SS8050KE Transistor(NPN)

Feature

- Good current characters
- Small saturable voltage drop
- High Breakdown voltage

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

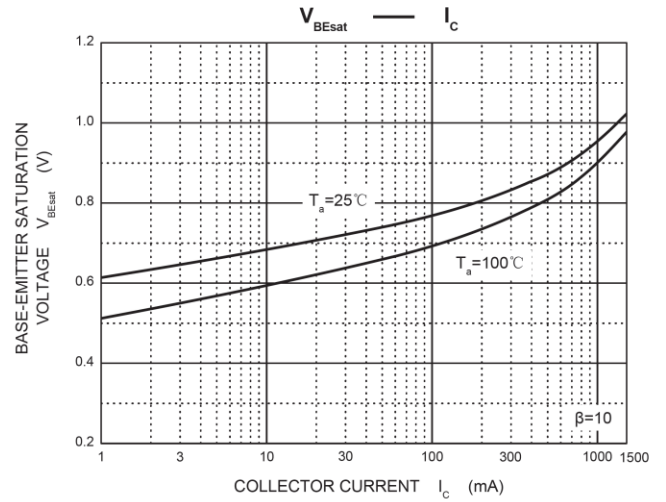
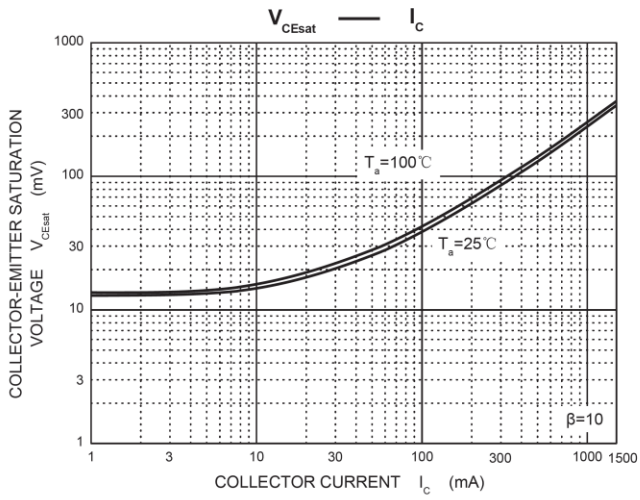
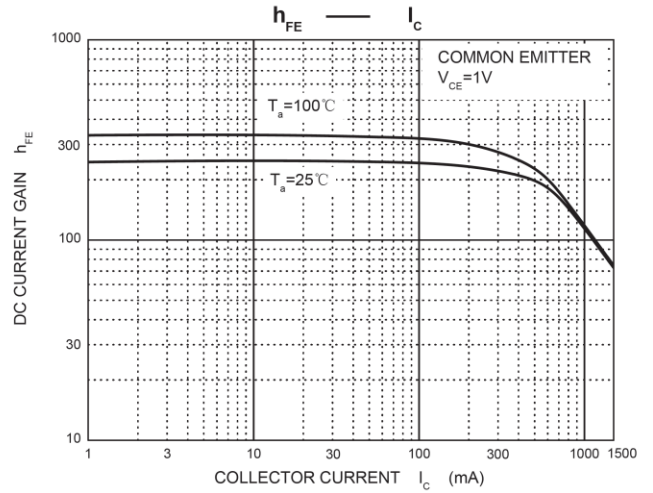
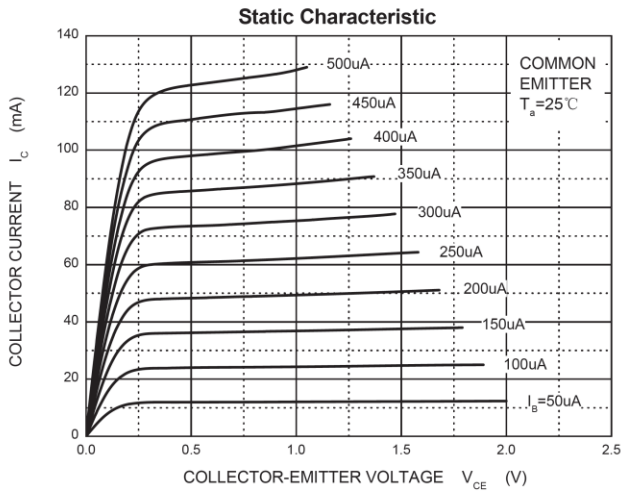
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	1.5	A
Power Dissipation	P _d	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C



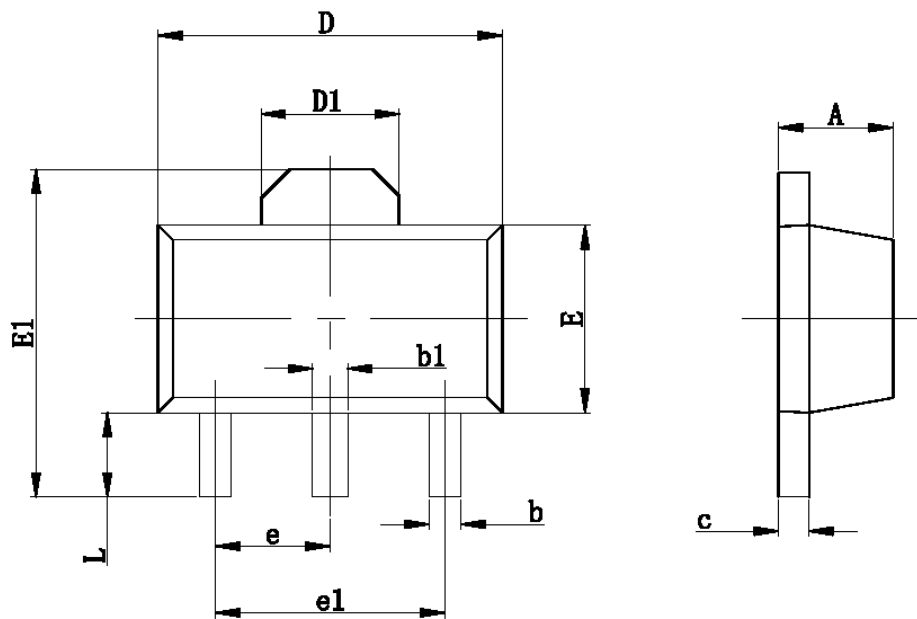
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =100μA, I _B =0	20		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5		V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0		1	uA
Collector cut-off current	I _{CEO}	V _{CE} =20V, I _B =0		1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		1	uA
DC current gain	h _{FE}	V _{CE} =1V, I _C =100mA	160	320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B =80mA		0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =800mA, I _B =80mA		1.4	V
Transition frequency	f _T	V _{CE} = 6V, I _C =20mA, f=30MHz	150		MHZ

Typical Characteristics



SOT-89-3L Package Outline Dimensions



Symbol	Dimensions in millimeters		Dimensions in inches	
	Min.	Max.	Min.	Max.
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550REF		0.061REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500TYP		0.060TYP	
e1	3.000TYP		0.118TYP	
L	0.900	1.200	0.035	0.047